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# PIMC31

# 500 mA, 50 V NPN/PNP double resistor-equipped transistor; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

Rev. 01 — 24 March 2009

**Product data sheet** 

# 1. Product profile

### 1.1 General description

500 mA, 50 V NPN/PNP double Resistor-Equipped Transistor (RET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PIMN31

#### 1.2 Features

- 500 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

### 1.3 Applications

- Digital application in automotive and industrial segments
- Switching loads

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol         | Parameter                   | Conditions                | Min | Тур | Max | Unit |
|----------------|-----------------------------|---------------------------|-----|-----|-----|------|
| Per transis    | stor; for the PNP transiste | or with negative polarity |     |     |     |      |
| $V_{CEO}$      | collector-emitter voltage   | open base                 | -   | -   | 50  | V    |
| I <sub>O</sub> | output current              |                           | -   | -   | 500 | mA   |
| R1             | bias resistor 1 (input)     |                           | 0.7 | 1   | 1.3 | kΩ   |
| R2/R1          | bias resistor ratio         |                           | 9   | 10  | 11  |      |



# 500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

# 2. Pinning information

Table 2. Pinning

| Table 2. | Filling                |                    |                          |
|----------|------------------------|--------------------|--------------------------|
| Pin      | Description            | Simplified outline | Graphic symbol           |
| 1        | GND (emitter) TR1      |                    |                          |
| 2        | input (base) TR1       | <u> </u>           | 6 5 4                    |
| 3        | output (collector) TR2 |                    |                          |
| 4        | GND (emitter) TR2      |                    | R1 R2                    |
| 5        | input (base) TR2       |                    | TR1                      |
| 6        | output (collector) TR1 |                    | R2 R1 R1 1 2 3 006999143 |

# 3. Ordering information

Table 3. Ordering information

| Type number | Package | Package  |         |  |  |
|-------------|---------|--|---------|--|--|
|             | Name    | Description                                      | Version |  |  |
| PIMC31      | SC-74   | plastic surface-mounted package (TSOP6); 6 leads | SOT457  |  |  |

# 4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PIMC31      | ZH           |

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

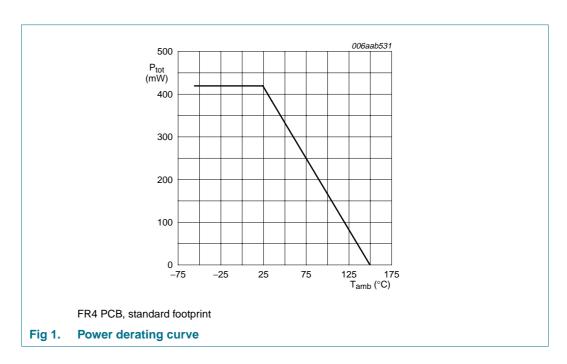
| Symbol      | Parameter                    | Conditions             | Min | Max        | Unit |
|-------------|------------------------------|------------------------|-----|------------|------|
| Per transis | stor; for the PNP transistor | with negative polarity |     |            |      |
| $V_{CBO}$   | collector-base voltage       | open emitter           | -   | 50         | V    |
| $V_{CEO}$   | collector-emitter voltage    | open base              | -   | 50         | V    |
| $V_{EBO}$   | emitter-base voltage         | open collector         | -   | 5          | V    |
| VI          | input voltage TR1            |                        |     |            |      |
|             | positive                     |                        | -   | +10        | V    |
|             | negative                     |                        | -   | <b>-</b> 5 | V    |
|             | input voltage TR2            |                        |     |            |      |
|             | positive                     |                        | -   | +5         | V    |
|             | negative                     |                        | -   | -10        | V    |

#### 500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

**Table 5.** Limiting values ...continued In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions                  | Min          | Max  | Unit |
|------------------|-------------------------|-----------------------------|--------------|------|------|
| $I_{O}$          | output current          |                             | -            | 500  | mA   |
| $P_{tot}$        | total power dissipation | $T_{amb} \le 25  ^{\circ}C$ | <u>[1]</u> _ | 290  | mW   |
| Per device       |                         |                             |              |      |      |
| P <sub>tot</sub> | total power dissipation | $T_{amb} \le 25  ^{\circ}C$ | <u>[1]</u> _ | 420  | mW   |
| T <sub>j</sub>   | junction temperature    |                             | -            | 150  | °C   |
| T <sub>amb</sub> | ambient temperature     |                             | <b>–55</b>   | +150 | °C   |
| T <sub>stg</sub> | storage temperature     |                             | -65          | +150 | °C   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



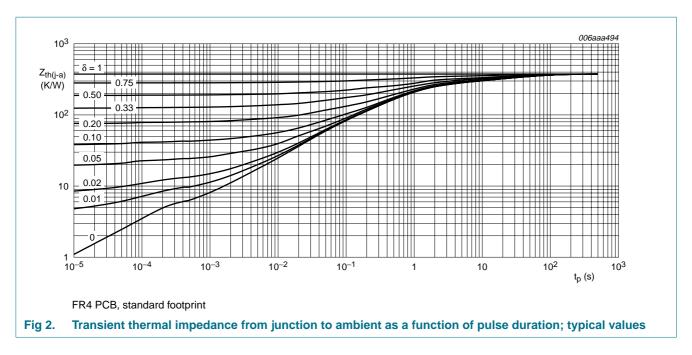
# 6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol               | Parameter  | Conditions  | Min          | Тур | Max | Unit |
|----------------------|--|-------------|--------------|-----|-----|------|
| Per transis          | stor   |             |              |     |     |      |
| $R_{th(j-a)}$        | thermal resistance from junction to ambient      | in free air | <u>[1]</u> - | -   | 431 | K/W  |
| $R_{th(j-sp)}$       | thermal resistance from junction to solder point |             | -            | -   | 105 | K/W  |
| Per device           |  |             |              |     |     |      |
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient      | in free air | <u>[1]</u> - | -   | 298 | K/W  |

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

#### 500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$



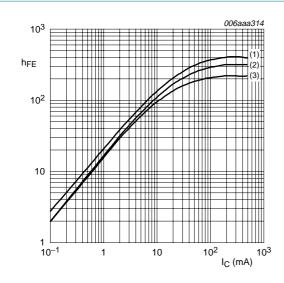
# 7. Characteristics

Table 7. Characteristics

 $T_{amb}$  = 25 °C unless otherwise specified.

| Symbol             | Parameter                            | Conditions   | Min | Тур | Max  | Unit |
|--------------------|--------------------------------------|--|-----|-----|------|------|
| Per transis        | stor; for the PNP transi             | stor with negative polarity                                    |     |     |      |      |
| I <sub>CBO</sub>   | collector-base cut-off current       | $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$                     | -   | -   | 100  | nA   |
| I <sub>CEO</sub>   | collector-emitter<br>cut-off current | $V_{CE} = 50 \text{ V}; I_{B} = 0 \text{ A}$                   | -   | -   | 0.5  | μΑ   |
| I <sub>EBO</sub>   | emitter-base cut-off current         | $V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$                      | -   | -   | 0.72 | mA   |
| h <sub>FE</sub>    | DC current gain                      | $V_{CE} = 5 \text{ V}; I_{C} = 50 \text{ mA}$                  | 70  | -   | -    |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | $I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}$                    | -   | -   | 0.3  | V    |
| $V_{I(off)}$       | off-state input voltage              | $V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$                | 0.3 | 0.6 | 1    | V    |
| V <sub>I(on)</sub> | on-state input voltage               | $V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$                | 0.4 | 0.8 | 1.4  | V    |
| R1                 | bias resistor 1 (input)              |  | 0.7 | 1   | 1.3  | kΩ   |
| R2/R1              | bias resistor ratio                  |  | 9   | 10  | 11   |      |
| C <sub>c</sub>     | collector capacitance                | $V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$<br>f = 1 MHz |     |     |      |      |
|                    | TR1 (NPN)                            |  | -   | 7   | -    | pF   |
|                    | TR2 (PNP)                            |  | -   | 11  | -    | pF   |

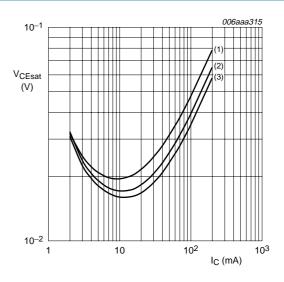
#### 500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$



$$V_{CE} = 5 V$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

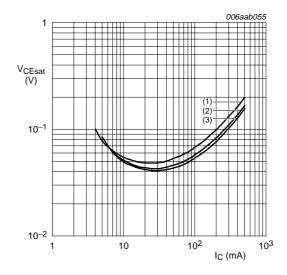
Fig 3. TR1 (NPN): DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

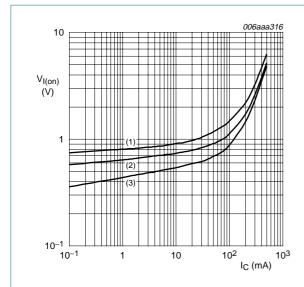


$$I_{\rm C}/I_{\rm B}=50$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 5. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

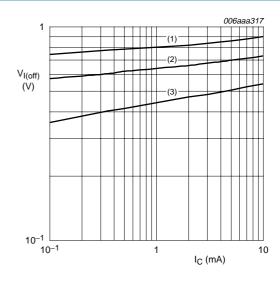
### 500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$



$$V_{CE} = 0.3 \text{ V}$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 6. TR1 (NPN): On-state input voltage as a function of collector current; typical values

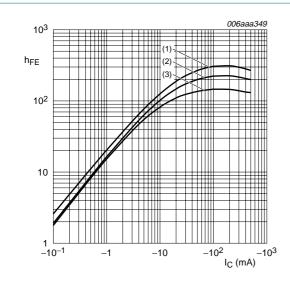


$$V_{CE} = 5 V$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 7. TR1 (NPN): Off-state input voltage as a function of collector current; typical values

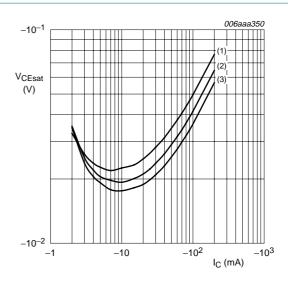
### 500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$



$$V_{CE} = -5 \text{ V}$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

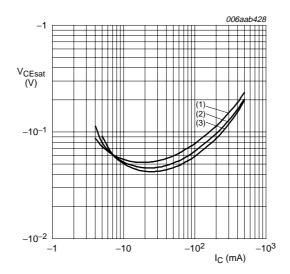
Fig 8. TR2 (PNP): DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 9. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

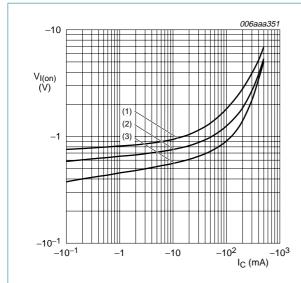


$$I_{\rm C}/I_{\rm B}=50$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

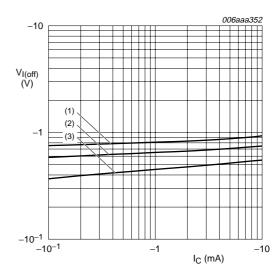
### 500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$



$$V_{CE} = -0.3 \text{ V}$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 11. TR2 (PNP): On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

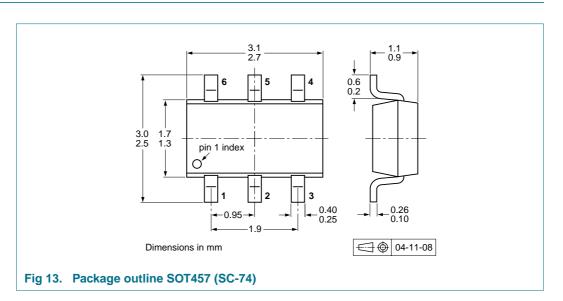
500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$ 

# 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 9. Package outline



# 10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | Description                        |            | Packing q | uantity |
|-------------|---------|------------------------------------|------------|-----------|---------|
|             |         |                                    |            | 3000      | 10000   |
| PIMC31      | SOT457  | 4 mm pitch, 8 mm tape and reel; T1 | [2]        | -115      | -135    |
|             |         | 4 mm pitch, 8 mm tape and reel; T2 | <u>[3]</u> | -125      | -165    |

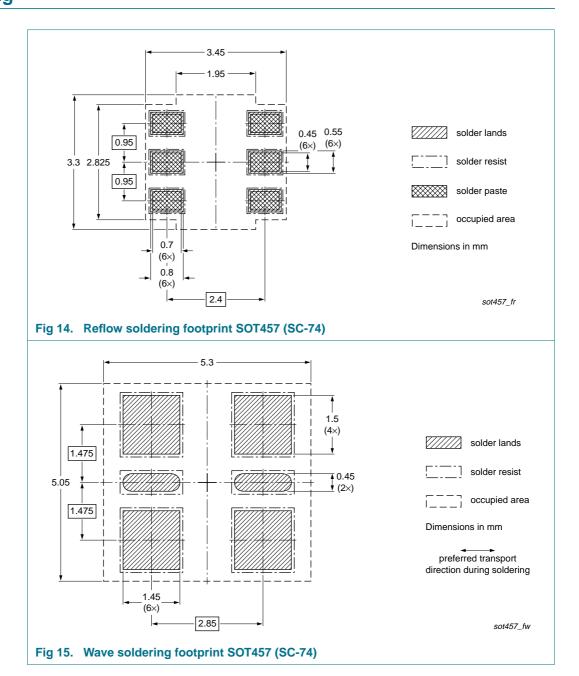
<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

[3] T2: reverse taping

### 500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

# 11. Soldering



500 mA, 50 V NPN/PNP double RET; R1 = 1 kΩ, R2 = 10 kΩ

# 12. Revision history

# Table 9. Revision history

| Document ID | Release date | Data sheet status  | Change notice | Supersedes |
|-------------|--------------|--------------------|---------------|------------|
| PIMC31_1    | 20090324     | Product data sheet | -             | -          |

#### 500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

# 13. Legal information

#### 13.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

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# 500 mA, 50 V NPN/PNP double RET; R1 = 1 k $\Omega$ , R2 = 10 k $\Omega$

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